K. Memory (Design & Process Technology) 분과
[TG2-K] Emerging Memory I

TG2-K-1 **10:45~11:15**	**[초청]** **TBA** 유향근 *SK하이닉스*
TG2-K-2 **11:15~11:45**	**[초청]** **Ferroelectric $Hf_{0.5}Zr_{0.5}O_2$ Thin Films** Si Joon Kim *Department of Electrical and Electronics Engineering, Kangwon National University*
TG2-K-3 **11:45~12:00**	**Highly Linear and Symmetric Synaptic Function of a Memristive Device for Spiking Neural Network System** Jin Joo Ryu[1,2], Kanghyeok Jeon[1], Min Kyu Yang[3], Chunjoong Kim[2], and Gun Hwan Kim[1] *[1]Division of Advanced Materials, KRICT, [2]Department of Materials Science and Engineering, Chungnam National University, [3]Division of IT Convergence Engineering, Sahmyook University*
TG2-K-4 **12:00~12:15**	**The Origin of Incremental Step Pulse Programming (ISPP) Slope Degradation in NAND Flash Memory** Kihoon Nam, Chanyang Park, Jun-Sik Yoon, Hyun-Dong Jang, and Rock-Hyun Ba다 *Department of Electrical Engineering, POSTECH*
TG2-K-5 **12:15~12:30**	**Effect of Interface Roughness on Program/Erase Efficiency for 3D Vertical NAND Flash Memory Applications** Yongjin Cho, Hyeongwan Oh, Gilsang Yoon, Jaeseok Jin, Donghyun Go, Jounghun Park, and Jeongsoo Lee *Department of Electrical Engineering, POSTECH*